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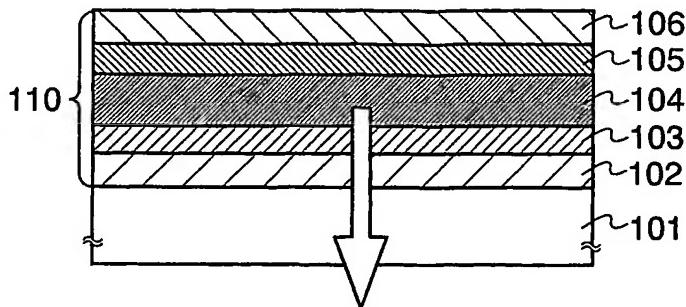
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(54) Title: LIGHT EMITTING ELEMENT AND DISPLAY DEVICE USING THE SAME



WO 2006/035952 A1 interposed between a layer containing an oxide semiconductor and/or metal oxide and a material having a higher hole transporting property than an electron transporting property, and a layer containing an oxide semiconductor and/or metal oxide, a material having a higher electron transporting property than a hole transporting property and a material which can donate electrons to the material having a higher electron transporting property than a hole transporting property.

(57) Abstract: An object of the invention is to provide a highly reliable light emitting element with low drive voltage and longer life than a conventional light emitting element, and a display device using the light emitting element. A light emitting element according to the invention comprises a plurality of layers which is interposed between a pair of electrodes, in which at least one of the plurality of layers is formed of a layer containing a light emitting material, and the layer containing a light emitting material is